HALOGEN

FREE



1.2 A Slew Rate Controlled Load Switch

DESCRIPTION

The SiP4282 series is a slew rate controlled high side switch. The switch is of a low on resistance p-channel MOSFET that supports continuous current up to 1.2 A.

The SiP4282 series operates with an input voltage from 1.8 V to 5.5 V. It offers under voltage lock out that turns the switch off when an input under voltage condition exists. The "A" option without UVLO extends the minimum operation voltage from 1.8 V down to 1.5 V. The SiP4282 is available in two different versions of slew rates, 100 µs and 1 ms. The SiP4282 series integrates load discharge circuit to ensure the discharge of capacitive load when the switch is disabled.

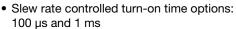
The SiP4282 features low input logic level to interface with low control voltage from microprocessors. This device has a very low operating current (typically 2.5 μ A for SiP4282 and 50 pA for SiP4282A).

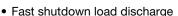
The SiP4282 is available in lead (Pb)-free package options including 6 pin PowerPAK® SC-75-6, and 4 pin TDFN4 1.2 mm x 1.6 mm DFN4 packages. The operation temperature range is specified from -40 °C to +85 °C.

The SiP4282 compact package options, operation voltage range, and low operating current make it a good fit for battery power applications.

FEATURES

- 1.8 V to 5.5 V input voltage range for SiP4282
- 1.5 V to 5.5 V input voltage range for SiP4282A
- Very low R_{DS(on)}, typically 105 mW at 5 V and 175 mW at 3 V





- Low quiescent current, 4 μA for SiP4282
- Low quiescent current, 1 μA for SiP4282A
- Low shutdown current < 1 μA
- UVLO of 1.4 V for SiP4282
- PowerPAK SC-75 1.6 mm x 1.6 mm and TDFN4 1.2 mm x 1.6 mm packages
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Cellular telephones
- Digital still cameras
- Personal digital assistants (PDA)
- Hot swap supplies
- Notebook computers
- · Personal communication devices
- Portable Instruments

TYPICAL APPLICATION CIRCUIT

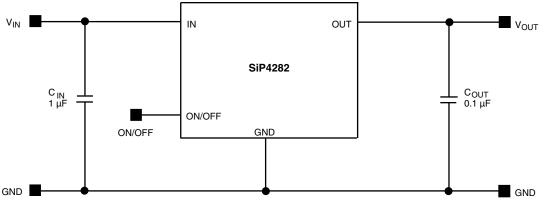


Fig. 1 - SiP4282 Typical Application Circuit

| ORDERING INFORMATION | | | | | | | | | |
|----------------------|-----------------|------------------|-----------------------|---------|--------------------|--|--|--|--|
| TEMPERATURE RANGE | PACKAGE | SLEW RATE (TYP.) | UNDER VOLTAGE LOCKOUT | MARKING | PART NUMBER | | | | |
| -40 °C to +85 °C | PowerPAK | 100 μs | No | LExxx | SiP4282ADVP3-T1GE3 | | | | |
| | SC-75-6 | 100 μs | Yes | LFxxx | SiP4282DVP3-T1GE3 | | | | |
| | TDFN4 1.2 x 1.6 | 100 μs | No | Bx | SiP4282ADNP3-T1GE4 | | | | |
| | | 100 µs | Yes | Cx | SiP4282DNP3-T1GE4 | | | | |

Note

xxx = lot code

Vishay Siliconix

| ABSOLUTE MAXIMUM RATIN | IGS | | |
|---|--|-------------------------------|------|
| PARAMETER | | LIMIT | UNIT |
| Supply input voltage (V _{IN}) | | -0.3 to 6 | |
| Enable input voltage (V _{ON / OFF}) | | -0.3 to 6 | V |
| Output voltage (V _{OUT}) | | -0.3 to V _{IN} + 0.3 | |
| Maximum continuous switch current (Imax | (.) | 1.4 | |
| Manipular de la compact (L.) V | V _{IN} ≥ 2.5 V | 3 | Α |
| Maximum pulsed current (I _{DM}) V _{IN} | V _{IN} < 2.5 V | 1.6 | |
| ESD rating (HBM) | · | 4000 | V |
| Junction temperature (T _J) | | -40 to +125 | °C |
| The arrest was interest (0) 3 | 6 pin PPAK SC75 b | 90 | °C/M |
| Thermal resistance (θ _{JA}) ^a | 4 pin TDFN4 1.2 mm x 1.6 mm ^c | 170 | °C/W |
| Device fineingtion (D.) 3 | 6 pin PPAK SC75 b | 610 | \/ |
| Power fissipation (P _D) ^a | 4 pin TDFN4 1.2 mm x 1.6 mm ^c | 324 | mW |

Notes

- Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings
 only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the
 specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability
- a. Device mounted with all leads and power pad soldered or welded to PC board
- b. Derate 11.1 mW/°C above $T_A = 70$ °C
- c. Derate 5.9 mW/ $^{\circ}$ C above T_A = 70 $^{\circ}$ C, see PCB layout

| RECOMMENDED OPERATING RANGE | | | | | | | |
|---|------------|------|--|--|--|--|--|
| PARAMETER | LIMIT | UNIT | | | | | |
| Input voltage range (V _{IN}) for SiP4282 version | 1.8 to 5.5 | V | | | | | |
| Input voltage range (V _{IN}) for SiP4282A version | 1.5 to 5.5 | V | | | | | |
| Operating temperature range | -40 to +85 | °C | | | | | |

| SPECIFICATIONS | | | | | | | | |
|---|------------------------|---|---|---------|--------|---|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED | LIMITS -40 °C to +85 °C | | | UNIT | | |
| | | $V_{IN} = 5$, $T_A = -40$ °C to +85 °C (typical values are at $T_A = 25$ °C) | MIN. a | TYP. b | MAX. a | • | | |
| Operating voltage ^c | V | For SiP4282xxx | 1.8 | - | 5.5 | | | |
| Operating voltage | V _{IN} | For SiP4282Axxx | 1.5 | - | 5.5 | V | | |
| Under voltage lockout | V _{UVLO} | For SiP4282xxx, V _{IN} falling | 1 | 1.4 | 1.8 | | | |
| Under voltage lockout hysteresis | V _{UVLO(hyh)} | For SiP4282xxx | - | 250 | - | mV | | |
| 0 | ΙQ | For SiP4282xxx, on / off = active | - | 2.5 | 4 | μА | | |
| Quiescent current | | For SiP4282Axxx, on / off = active | - | 0.00005 | 1 | | | |
| | | V _{IN} = 5 V, I _L = 500 mA, T _A = 25 °C | - | 105 | 230 | mΩ | | |
| | | V _{IN} = 4.2 V, I _L = 500 mA, T _A = 25 °C | - | 110 | 250 | | | |
| On-resistance | R _{DS(on)} | V _{IN} = 3 V, I _L = 500 mA, T _A = 25 °C | - | 135 | 290 | | | |
| | DO(OH) | V _{IN} = 1.8 V, I _L = 500 mA, T _A = 25 °C | - | 230 | 480 | | | |
| | | For SiP4282Axxx, V_{IN} = 1.5 V, I_L = 500 mA, T_A = 25 °C | - | 350 | 520 | | | |
| On-resistance temp. coefficient | TC _{RDS} | | - | 2800 | - | ppm/°C | | |
| | | For SiP4282Axxx, $V_{IN} \ge 1.5 \text{ V to} < 1.8 \text{ V}$ | P4282Axxx, V _{IN} ≥ 1.5 V to < 1.8 V | | 0.3 | | | |
| On / off input low voltage ^d | V _{IL} | $V_{IN} \ge 1.8 \text{ V to} < 2.7 \text{ V}$ | = | - | 0.4 | V | | |
| | | $V_{IN} \ge 2.7 \text{ V to} \le 5.5 \text{ V}$ | - | - | 0.6 | | | |

www.vishay.com

Vishay Siliconix

| SPECIFICATIONS | | | | | | | | |
|--|---------------------------------------|---|----------------------------|--------|--------|------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED | LIMITS -40 °C to +85 °C | | | UNIT | | |
| | OTMBOL | $V_{IN} = 5$, $T_A = -40$ °C to $+85$ °C (typical values are at $T_A = 25$ °C) | MIN. a | TYP. b | MAX. a | • | | |
| | | $V_{IN} \geq 1.5 \; V \; to < 2.7 \; V$ | 1.3 | - | - | | | |
| On / off input high voltage ^d | V _{IH} | $V_{IN} \geq 2.7 \; V \; to < 4.2 \; V$ | 1.5 | - | - | V | | |
| | | $V_{IN} \geq 4.2 \; V \; to \leq 5.5 \; V$ | 1.8 | - | - | | | |
| On / off input leakage | I _{SINK} | $V_{On / off} = 5.5 V$ | - | - | 1 | μΑ | | |
| Output pulldown resistance | R _{PD} | On / off = Inactive, $T_A = 25$ °C | - | 180 | 250 | Ω | | |
| SiP4282xxx3 and SiP4282Axxx3 Ver | SiP4282xxx3 and SiP4282Axxx3 Versions | | | | | | | |
| Output turn-on delay time | t _{d(on)} | $V_{IN}=5$ V, $R_{LOAD}=10~\Omega,T_{A}=25~^{\circ}C$ | - | 20 | 40 | | | |
| Output turn-on rise time | t _(on) | V_{IN} = 5 V, R_{LOAD} = 10 Ω , T_A = 25 °C | - | 140 | 180 | μs | | |
| Output turn-off delay time | t _{d(off)} | V_{IN} = 5 V, R_{LOAD} = 10 Ω , T_A = 25 °C | - | 4 | 10 | | | |

Notes

- a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- c. Part requires minimum start-up of $V_{IN} \ge 2 \text{ V}$ to ensure operation down to 1.8 V
- d. For V_{IN} outside this range consult typical on / off threshold curve

PIN CONFIGURATION

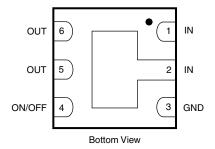


Fig. 2 - PPAK SC75-6 Package

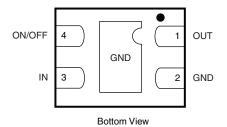


Fig. 3 - TDFN4 1.2 mm x 1.6 mm Package

| PIN DESCRIPTION | | | | | | | | |
|-----------------|-------|--------|--|--|--|--|--|--|
| PIN NUMB | ER | NAME | FUNCTION | | | | | |
| PPAK | TDFN4 | NAME | FUNCTION | | | | | |
| 1, 2 | 3 | IN | This pin is the p-channel MOSFET source connection. Bypass to ground through a 1 µF capacitor | | | | | |
| 3 | 2 | GND | Ground connection | | | | | |
| 4 | 4 | ON/OFF | Enable input | | | | | |
| 5, 6 | 1 | OUT | This pin is the p-channel MOSFET drain connection. Bypass to ground through a 0.1 µF capacitor | | | | | |



TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

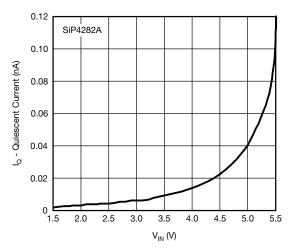


Fig. 4 - Quiescent Current vs. Input Voltage

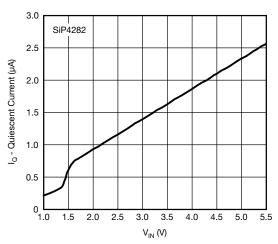


Fig. 5 - Quiescent Current vs. Input Voltage

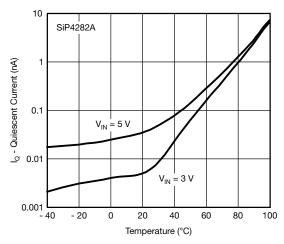


Fig. 6 - Quiescent Current vs. Temperature

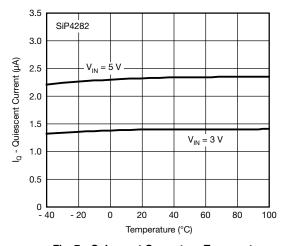


Fig. 7 - Quiescent Current vs. Temperature

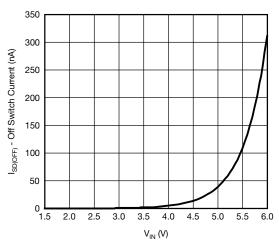


Fig. 8 - Off Switch Current vs. Input Voltage

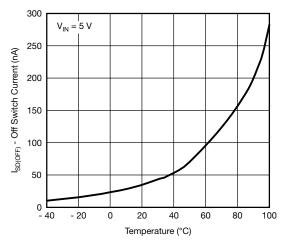


Fig. 9 - Off Switch Current vs. Temperature



TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

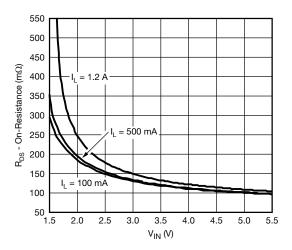


Fig. 10 - R_{DS(on)} vs. Input Voltage

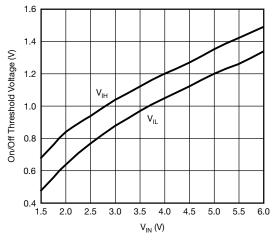


Fig. 13 - On / Off Threshold vs. Input Voltage

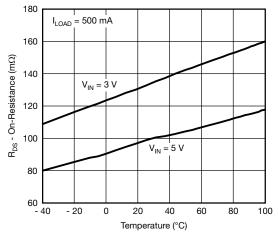


Fig. 11 - R_{DS(on)} vs. Temperature

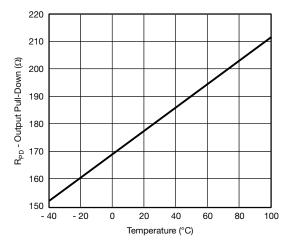
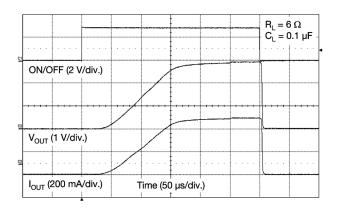


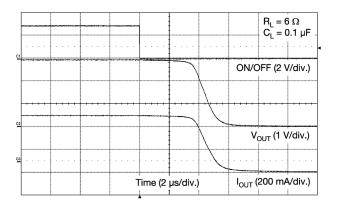
Fig. 12 - Output Pull-Down Resistance vs. Temperature



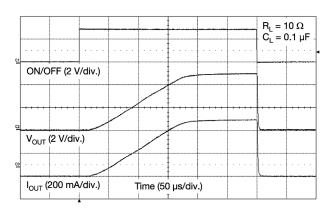
TYPICAL WAVEFORMS



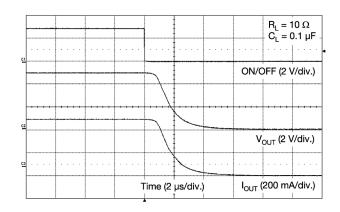
SiP4282xxx3 and SiP4282Axxx3 Switching (V_{IN} = 3 V)



SiP4282xxx3 and SiP4282Axxx3 Turn-Off $(V_{IN} = 3 V)$



SiP4282xxx3 and SiP4282Axxx3 Switching $(V_{IN} = 5 V)$



SiP4282xxx3 and SiP4282Axxx3 Turn-Off (V_{IN} = 5 V)



BLOCK DIAGRAM

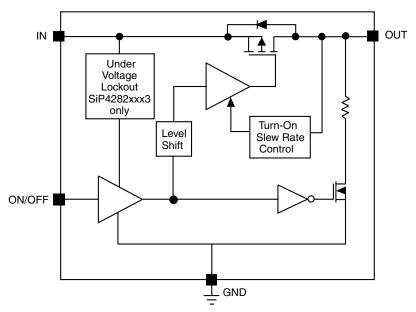


Fig. 14 - SiP4282 Functional Block Diagram

PCB LAYOUT

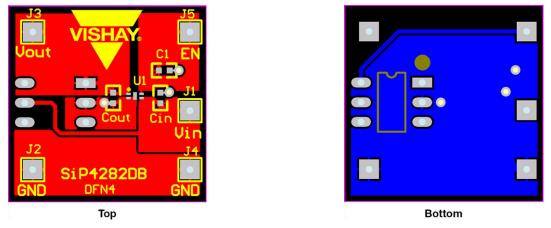


Fig. 15 - TDFN4 1.2 mm x 1.6 mm PCB Layout

Vishay Siliconix

DETAILED DESCRIPTION

The SiP4282 is a p-channel MOSFET power switches designed for high-side slew rate controlled load-switching applications. Once turned on, the slew-rate control circuitry is activated and current is ramped in a linear fashion until it reaches the level required for the output load condition. This is accomplished by first elevating the gate voltage of the MOSFET up to its threshold voltage and then by linearly increasing the gate voltage until the MOSFET becomes fully enhanced. At this point, the gate voltage is then quickly increased to the full input voltage to reduce R_{DS(on)} of the MOSFET switch and minimize any associated power losses.

All versions features a shutdown output discharge circuit which is activated at shutdown (when the part is disabled through the on / off pin) and discharges the output pin through a small internal resistor hence, turning off the load. For SiP4282-3, in instances where the input voltage falls below 1.4 V (typically) the under voltage lock-out circuitry protects the MOSFET switch from entering the saturation region or operation by shutting down the chip.

APPLICATION INFORMATION

Input Capacitor

While a bypass capacitor on the input is not required, a 1 μ F or larger capacitor for C_{IN} is recommended in almost all applications. The bypass capacitor should be placed as physically close as possible to the SiP4282 to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

Output Capacitor

A 0.1 μ F capacitor or larger across V_{OUT} and GND is recommended to insure proper slew operation. C_{OUT} may be increased without limit to accommodate any load transient condition with only minimal affect on the SiP4282 turn on slew rate time. There are no ESR or capacitor type requirement.

Enable

The on / off pin is compatible with both TTL and CMOS logic voltage levels.

Protection Against Reverse Voltage Condition

The p-channel MOSFET pass transistor has an intrinsic diode that is reversed biased when the input voltage is greater than the output voltage. Should V_{OUT} exceed V_{IN} , this intrinsic diode will become forward biased and allow excessive current to flow into the IC thru the V_{OUT} pin and potentially damage the IC device. Therefore extreme care should be taken to prevent V_{OUT} from exceeding V_{IN} .

In conditions where V_{OUT} exceeds V_{IN} a Schottky diode in parallel with the internal intrinsic diode is recommended to protect the SiP4282.

Thermal Considerations

The SiP4282 is designed to maintain a constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 1.2 A, as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of 90 °C/W) the power pad of the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependent on the maximum junction temperature, T_J (max.) = 125 °C, the junction-to-ambient thermal resistance for the SC-75 PPAK package, $\theta_{J-A}=90$ °C/W, and the ambient temperature, T_A , which may be formulaically expressed as:

$$P \text{ (max.)} = \frac{T_J \text{ (max.)} - T_A}{\theta_{J-A}} = \frac{125 - T_A}{90}$$

It then follows that, assuming an ambient temperature of 70 °C, the maximum power dissipation will be limited to about 610 mW.

So long as the load current is below the 1.2 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the $R_{DS(on)}$ at the ambient temperature.

As an example let us calculate the worst case maximum load current at $T_A=70~^{\circ}\text{C}$. The worst case $R_{DS(on)}$ at 25 $^{\circ}\text{C}$ occurs at an input voltage of 1.8 V and is equal to 480 m Ω . The $R_{DS(on)}$ at 70 $^{\circ}\text{C}$ can be extrapolated from this data using the following formula

 $R_{DS(on)}$ (at 70 °C) = $R_{DS(on)}$ (at 25 °C) x (1 + T_C x ΔT)

Where T_C is 3300 ppm/°C. Continuing with the calculation we have

 $R_{DS(on)}$ (at 70 °C) = 480 m Ω x (1 + 0.0033 x (70 °C - 25 °C)) = 551 m Ω

The maximum current limit is then determined by

$$I_{LOAD}$$
 (max.) $< \sqrt{\frac{P \text{ (max.)}}{R_{DS(on)}}}$

which in case is 1.05 A. Under the stated input voltage condition, if the 1.05 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.



www.vishay.com

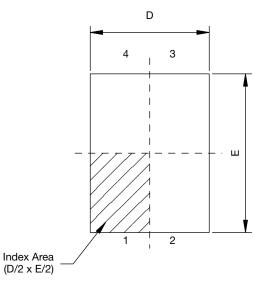
Vishay Siliconix

| PRODUCT SUMMARY | | | | |
|--|--|---|--|--|
| Part number | SiP4282 | SiP4282 | SiP4282A | SiP4282A |
| Description | 1.8 V to 5.5 V, 105 mΩ, 100 μ s rise time, with UVLO | $\begin{array}{c} 1.8\text{V to}5.5\text{V},105\text{m}\Omega,\\ 100\text{\mu s}\text{rise time, with}\\ \text{UVLO} \end{array}$ | 1.5 V to 5.5 V, 105 mΩ, 100 μs rise time | 1.5 V to 5.5 V, 105 mΩ, 100 µs rise time |
| Configuration | Single | Single | Single | Single |
| Slew rate time (µs) | 140 | 140 | 140 | 140 |
| On delay time (µs) | 20 | 20 | 20 | 20 |
| Input voltage min. (V) | 1.8 | 1.8 | 1.5 | 1.5 |
| Input voltage max. (V) | 5.5 | 5.5 | 5.5 | 5.5 |
| On-resistance at input voltage min. (mΩ) | 230 | 230 | 350 | 350 |
| On-resistance at input voltage max. (mΩ) | 105 | 105 | 105 | 105 |
| Quiescent current at input voltage min. (µA) | 1 | 1 | 0.00001 | 0.00001 |
| Quiescent current at input voltage max. (μA) | 2.5 | 2.5 | 0.00005 | 0.00005 |
| Output discharge (yes / no) | Yes | Yes | Yes | Yes |
| Reverse blocking (yes / no) | No | No | No | No |
| Continuous current (A) | 1.2 | 1.2 | 1.2 | 1.2 |
| Package type | TDFN4 | PowerPAK SC-75-6 | TDFN4 | PowerPAK SC-75-6 |
| Package size (W, L, H) (mm) | 1.2 x 1.6 x 0.5 | 0.75 x 1.6 x 0.5 | 1.2 x 1.6 x 0.5 | 0.75 x 1.6 x 0.5 |
| Status code | 2 | 2 | 2 | 2 |
| Product type | Slew rate | Slew rate | Slew rate | Slew rate |
| Applications | Computers, consumer, industrial, healthcare, networking, portable | Computers, consumer, industrial, healthcare, networking, portable | Computers, consumer, industrial, healthcare, networking, portable | Computers, consumer, industrial, healthcare, networking, portable |

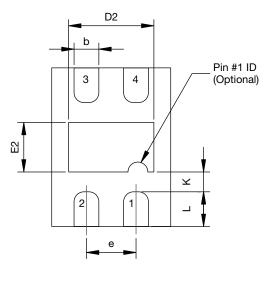
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65740.



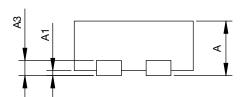
TDFN4 1.2 x 1.6 Case Outline







Bottom View



Side View

| DIM. | | MILLIMETERS | | INCHES | | | |
|------|-----------|----------------------|--------|------------|-------------------------------|-------|--|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| Α | 0.45 | 0.55 | 0.60 | 0.017 | 0.022 | 0.024 | |
| A1 | 0.00 | - | 0.05 | 0.00 | - | 0.002 | |
| A3 | 0. | 15 REF. or 0.127 REF | :_ (1) | | 0.006 or 0.005 ⁽¹⁾ | | |
| b | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 | |
| D | 1.15 | 1.20 | 1.25 | 0.045 | 0.047 | 0.049 | |
| D2 | 0.81 | 0.86 | 0.91 | 0.032 | 0.034 | 0.036 | |
| е | 0.50 BSC | | | 0.020 | | | |
| Е | 1.55 | 1.60 | 1.65 | 0.061 | 0.063 | 0.065 | |
| E2 | 0.45 | 0.50 | 0.55 | 0.018 | 0.020 | 0.022 | |
| K | 0.25 typ. | | | 0.010 typ. | | | |
| 1 | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 | |

Note

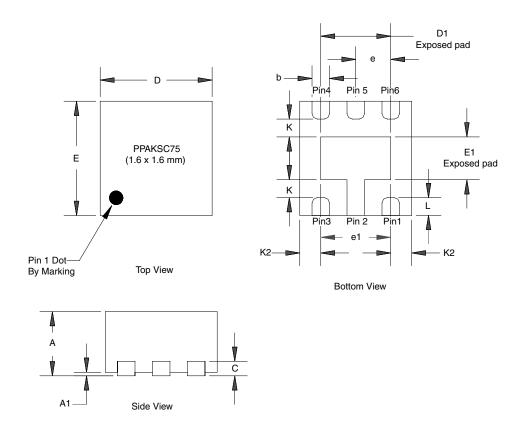
DWG: 5995

Revision: 18-Apr-16 1 Document Number: 65734

⁽¹⁾ The dimension depends on the leadframe that assembly house used.



PowerPAK® SC75-6L (Power IC only)



| | | MILLIMETERS | 3 | INCHES | | | |
|-----|----------|-------------|------|-----------|-----------|-------|--|
| DIM | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.032 | |
| A1 | 0 | - | 0.05 | 0 | - | 0.002 | |
| b | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 | |
| С | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| D | 1.55 | 1.60 | 1.65 | 0.0061 | 0.063 | 0.065 | |
| D1 | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 | |
| E | 1.55 | 1.60 | 1.65 | 0.061 | 0.063 | 0.065 | |
| E1 | 0.55 | 0.60 | 0.65 | 0.022 | 0.024 | 0.026 | |
| е | | 0.50 BSC | | | 0.020 BSC | | |
| e1 | 1.00 BSC | | | 0.039 BSC | | | |
| K | 0.15 | - | - | 0.006 | - | - | |
| K2 | 0.20 | - | - | 0.008 | | | |
| L | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 | |

ECN: S-60845-Rev. B, 22-May-06

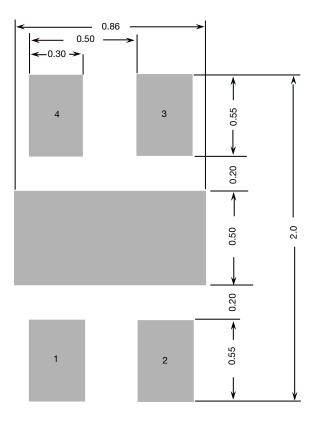
DWG: 5953

Document Number: 73850 www.vishay.com 22-May-06 1



Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR TDFN4 1.2 x 1.6



Recommended Minimum Pads Dimensions in mm

Document Number: 66558 www.vishay.com Revision: 05-Mar-10

Legal Disclaimer Notice



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.